EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((memory or storage) and single adj gate and two adj charge adj holding and current and second adj voltage and carrier and inject$5 and offset and electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:57

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3598787	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:29
L2	351084	1 and (non-volatile or nonvolatile or floating adj gate or flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:31
L3	15858	2 and (charge adj holding or spacer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:32
L4	119	3 and inject$5 with side with (charge adj holding or spacer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:33
L5	14	4 and single adj3 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:37
L6	120977	1 and substrate and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:38
L7	5492	6 and single adj3 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:39
L8	1949	7 and (spacer or charge adj hold$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:39
L9	855	8 and current with source with drain	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:40
L10	268	9 and offset with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:40
L11	105	10 and electrode with (charge adj hold$5 or spacer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:41

L12	96	11 and well	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/30 09:41